

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	3.0m Ω @10V	60A
	4.1m Ω @4.5V	

Feature

- Split Gate Trench Technology
- Low $R_{DS(on)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Application

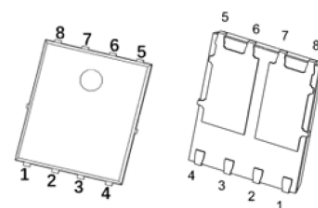
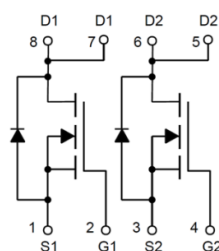
- Power Switching Application

MARKING:


T030ND03L = Device Code

XX = Date Code

Solid Dot = Green Indicator

PDFN5X6-8L

Schematic diagram

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ¹	$T_C = 25^\circ\text{C}$	I_D	60	A
	$T_C = 100^\circ\text{C}$	I_D	39	A
Pulsed Drain Current ²		I_{DM}	240	A
Single Pulsed Avalanche Current ³		I_{AS}	32	A
Single Pulsed Avalanche Energy ³		E_{AS}	256	mJ
Power Dissipation ⁵	$T_C = 25^\circ\text{C}$	P_D	37	W
Thermal Resistance from Junction to Ambient ⁶		$R_{\theta JA}$	60	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case		$R_{\theta JC}$	3.4	$^\circ\text{C/W}$
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~ +150	$^\circ\text{C}$

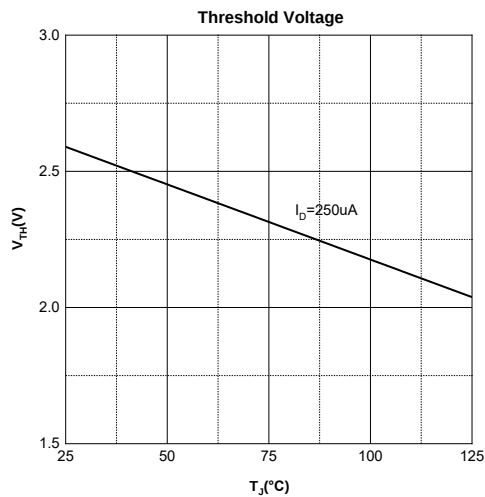
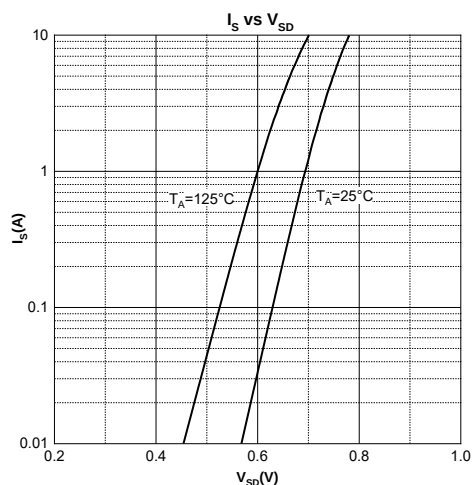
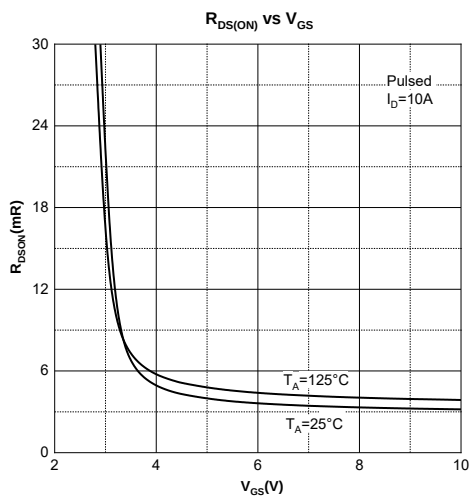
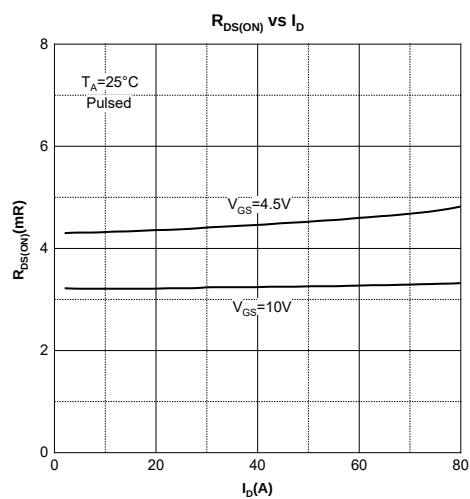
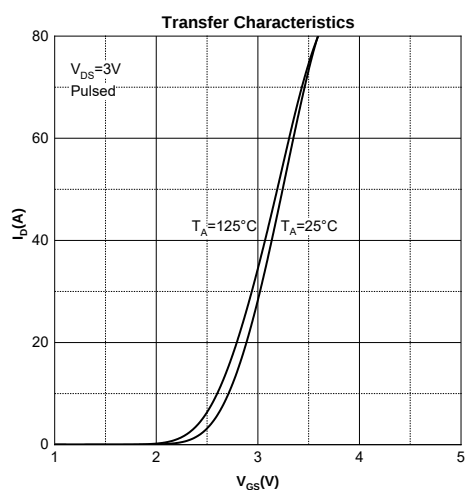
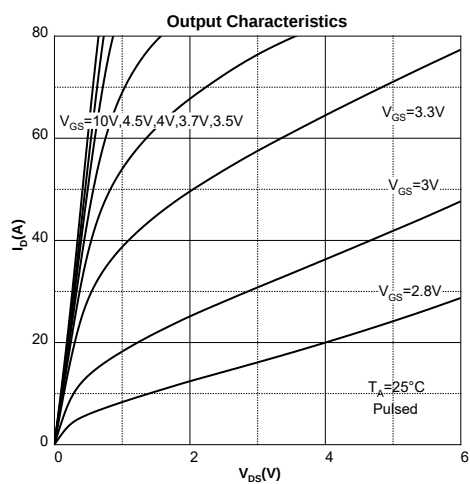
MOSFET ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

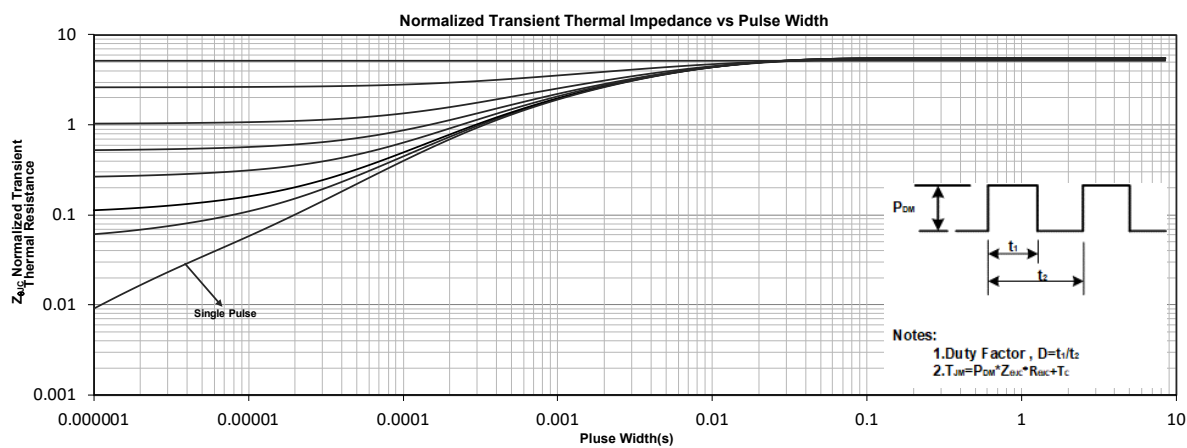
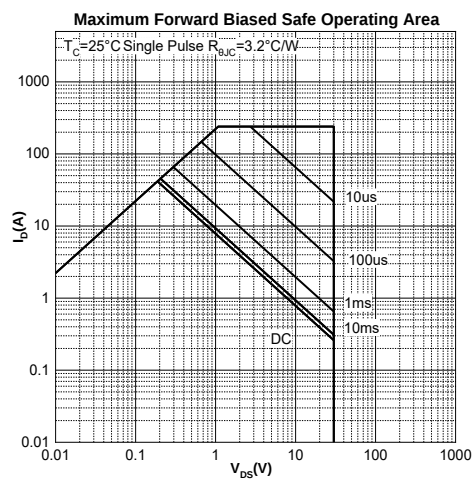
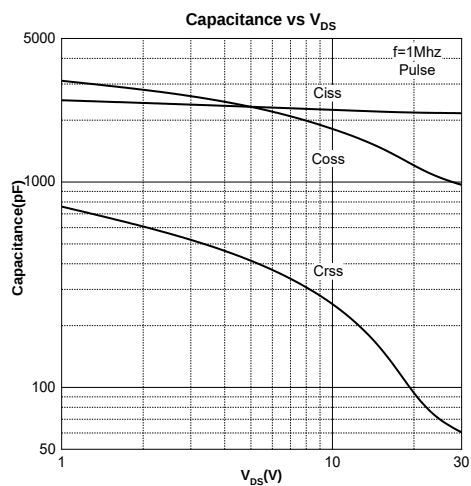
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
On Characteristics ⁴						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.7	3	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 10A		3.0	4.0	mΩ
		V _{GS} = 4.5V, I _D = 10A		4.1	5.4	
Dynamic Characteristics						
Input Capacitance	C _{iSS}	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz		2185		pF
Output Capacitance	C _{oSS}			1515		
Reverse Transfer Capacitance	C _{rSS}			141		
Gate Resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		3.4		Ω
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} = 15V, V _{GS} = 10V, I _D = 10A		38		nC
Gate-Source Charge	Q _{gs}			5.8		
Gate-Drain Charge	Q _{gd}			7.7		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15V, V _{GS} = 10V, I _D = 15A, R _G = 3Ω		10		ns
Turn-On Rise Time	t _r			41		
Turn-Off Delay Time	t _{d(off)}			29		
Turn-Off Fall Time	t _f			18		
Source-Drain Diode Characteristics						
Diode Forward Voltage ⁴	V _{SD}	V _{GS} = 0V, I _S = 10A			1.2	V

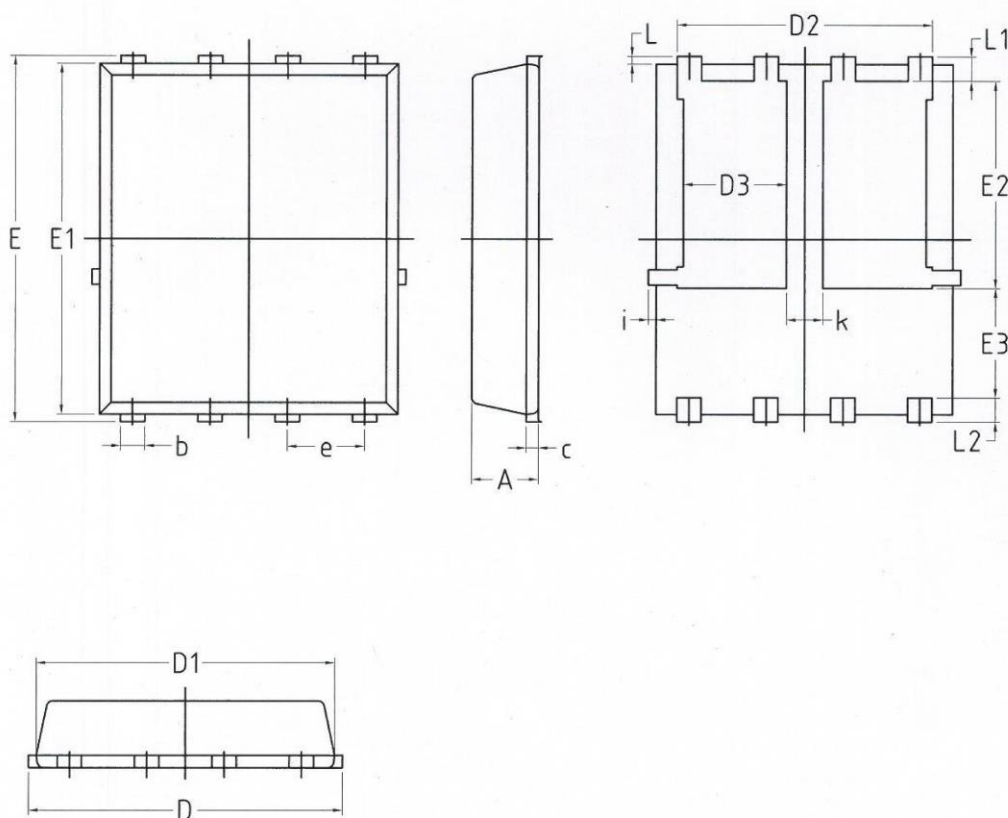
Notes :

- 1.The maximum current rating is limited by package. And device mounted on a large heatsink.
- 2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.
- 3.EAS condition: V_{DD} = 20V, V_{GS} = 10V, L = 0.5mH, R_G = 25Ω Starting T_J = 25°C.
- 4.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.
- 5.The power dissipation P_D is limited by T_{J(MAX)} = 150°C. And device mounted on a large heatsink
- 6.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C.

Typical Characteristics





PDFN5X6-8L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.030	1.170	0.041	0.046
b	0.340	0.480	0.013	0.019
c	0.203 BSC		0.008 BSC	
D	4.800	5.400	0.189	0.213
D1	4.800	5.000	0.189	0.197
D2	4.110	4.310	0.162	0.170
D3	1.600	1.800	0.063	0.071
E	5.950	6.150	0.234	0.242
E1	5.650	5.850	0.222	0.230
E2	3.300	3.500	0.130	0.138
E3	1.700	-	0.067	-
e	1.270 BSC		0.050 BSC	
L	0.050	0.250	0.002	0.010
L1	0.380	0.500	0.015	0.020
L2	0.380	0.500	0.015	0.020
i	-	0.180	-	0.007
k	0.500	0.700	0.020	0.028

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.